Docket No.: PHCF-03037US

HIR.130

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In repatent application of

Masatomo Shibata, et al.

Serial No · Not Yet Assigned Group Art Unit:

Not Yet Assigned

Filing Date:

Concurrently Herewith

Examiner:

Unknown

For:

POROUS SUBSTRATE AND FABRICATION METHOD THEREFOR, AND GaN SERIES SEMICONDUCTOR LAYERED SUBSTRATE AND

FABRICATION METHOD THEREFOR

Honorable Commissioner of Patents Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicant's duty of disclosure under 37 CFR §1.56, applicant respectfully brings the following documents listed on the attached form PTO-1449 and some of which are cited in the International Search Report (Form PCT/ISA/210), to the attention of the Examiner in charge of the aboveidentified application. Copies of the listed documents are provided herewith for the convenience of the Examiner. Further, in compliance with the concise explanation requirement under 37 CFR \$1.98(a)(3) for foreign language documents the relevance of these documents is discussed on pages 2 and 3 of the subject application. Further, for foreign documents English-language Abstract are attached.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted

Registration No. 34,386

Intellectual Property Law 8321 Old Courthouse Road, Suite 200 Vienna, VA 22182-3817 (703) 761-4100 Customer No. 21254

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Docket Number (Optional) PHCF-030371 Applicant(s)

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Masatomo Shibata, et al. Filing Date

Group Art Unit

Not Yet Assigned

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EXAMINER INITIAL	REP	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING I	
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/T.T./	Т	Chinkyo Kim, et al., " GaN by hydride vapor		otropic domain tilting along vertical Journal of Crystal Growth 208, 2000		_		ergro
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Form PTO-A820 (also form PTO-1449) P09A/REV05

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INFORMATION DISCLOSU CITATION
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Docket Number (Optional)
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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